Abstract Submitted
for the MAR14 Meeting of
The American Physical Society

Effect of annealing on electronic carrier transport properties of gamma-irradiated AlGaN/GaN high electron mobility transistors

ANUPAMA YADAV, CASEY SCHWARZ, MAX SHATKHIN, LUTHER WANG, ELENA FLITSIYAN, LEONID CHERNYAK, Department of Physics, University of Central Florida, LU LIU, YA HWANG, FAN REN, Department of Chemical Engineering, University of Florida, STEPHEN PEARTON, Department of Materials Science and Engineering, University of Florida, DEPARTMENT OF PHYSICS, UNIVERSITY OF CENTRAL FLORIDA COLLABORATION, DEPARTMENT OF CHEMICAL ENGINEERING, UNIVERSITY OF FLORIDA COLLABORATION, DEPARTMENT OF MATERIALS SCIENCE AND ENGINEERING, UNIVERSITY OF FLORIDA COLLABORATION — AlGaN/GaN High Electron Mobility Transistors were irradiated with ^{60}Co gamma-ray doses from 100Gy to 1000Gy, in order to analyze the effects of irradiation on the devices' transport properties. Temperature dependent Electron Beam Induced Current (EBIC) measurements, conducted on the devices before and after exposure to gamma-irradiation, allowed for the obtaining of activation energy related to radiation-induced defects due to nitrogen vacancies. Later, the devices were annealed at 200° C for 25 minutes. All the measurements were performed again to study the effect of annealing on the gamma-irradiated devices. Annealing of gamma-irradiated transistors shows that partial recovery of device performance is possible at this temperature. DC current-voltage measurements were also conducted on the transistors to assess the impact of gamma-irradiation and annealing on transfer, gate and drain characteristics.

Elena Flitsiyan
Department of Physics, University of Central Florida

Date submitted: 08 Nov 2013 Electronic form version 1.4